



FIG. 1
(Prior Art)

A cross-sectional view of a semiconductor device 200. The device includes a substrate 30 with a central region 31. A layer 52 is formed on the substrate. A layer 102 is formed on top of layer 52. A layer 104 is formed on top of layer 102. A layer 106 is formed on top of layer 104. A layer 34 is formed on top of layer 106. A layer 32 is formed on top of layer 34. A layer 36 is formed on top of layer 32. A layer 38 is formed on top of layer 36. A layer 40 is formed on top of layer 38. A layer 12 is formed on top of layer 40. A layer 202 is formed on top of layer 12. A layer 52 is formed on top of layer 202. A layer 30 is formed on top of layer 52.

FIG. 4